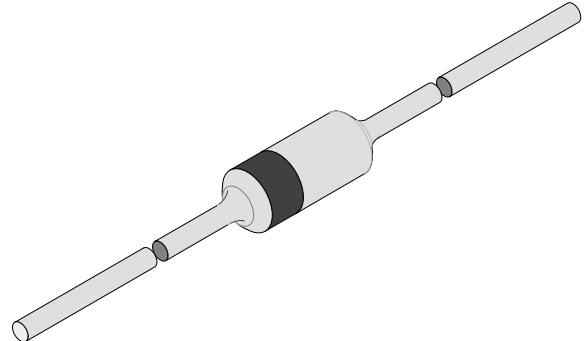


Silicon Epitaxial Planar Diodes

Features

- Electrically equivalent diodes: 1N4148 – 1N914
1N4448 – 1N914B



Applications

Extreme fast switches

94 9367

Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage			V_{RRM}	100	V
Reverse voltage			V_R	75	V
Peak forward surge current	$t_p=1\mu\text{s}$		I_{FSM}	2	A
Repetitive peak forward current			I_{FRM}	500	mA
Forward current			I_F	300	mA
Average forward current	$V_R=0$		I_{FAV}	150	mA
Power dissipation	$l=4\text{mm}, T_L=45^\circ\text{C}$		P_V	440	mW
	$l=4\text{mm}, T_L \leq 25^\circ\text{C}$		P_V	500	mW
Junction temperature			T_j	200	$^\circ\text{C}$
Storage temperature range			T_{stg}	-65...+200	$^\circ\text{C}$

Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4\text{mm}, T_L=\text{constant}$	R_{thJA}	350	K/W

Electrical Characteristics

$T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=5\text{mA}$	1N4448	V_F	0.62		0.72	V
	$I_F=10\text{mA}$	1N4148	V_F			1	V
	$I_F=100\text{mA}$	1N4448	V_F			1	V
Reverse current	$V_R=20\text{V}$		I_R			25	nA
	$V_R=20\text{V}, T_j=150^\circ\text{C}$		I_R			50	μA
	$V_R=75\text{V}$		I_R			5	μA
Breakdown voltage	$I_R=100\mu\text{A}, t_p/T=0.01, t_p=0.3\text{ms}$		$V_{(BR)}$	100			V
Diode capacitance	$V_R=0, f=1\text{MHz}, V_{HF}=50\text{mV}$		C_D			4	pF
Rectification efficiency	$V_{HF}=2\text{V}, f=100\text{MHz}$		η_r	45			%
Reverse recovery time	$I_F=I_R=10\text{mA}, i_R=1\text{mA}$		t_{rr}			8	ns
	$I_F=10\text{mA}, V_R=6\text{V}, i_R=0.1 \times I_R, R_L=100\Omega$		t_{rr}			4	ns

Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

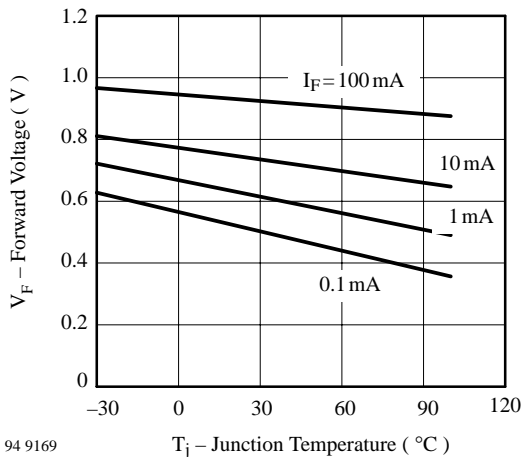


Figure 1. Forward Voltage vs. Junction Temperature

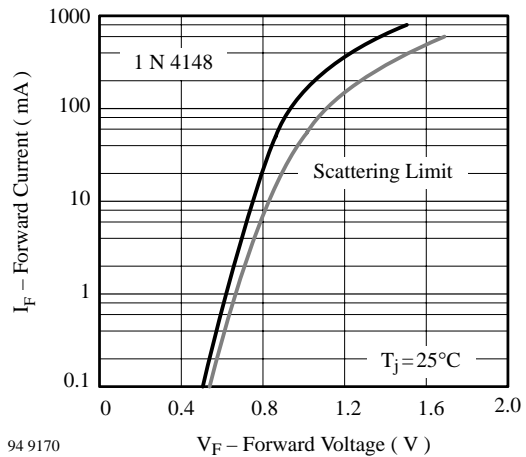


Figure 2. Forward Current vs. Forward Voltage

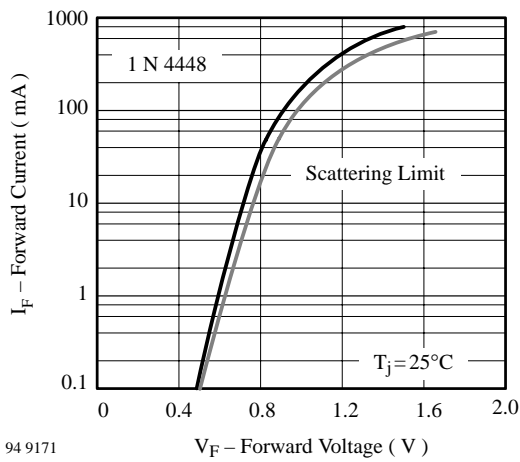


Figure 3. Forward Current vs. Forward Voltage

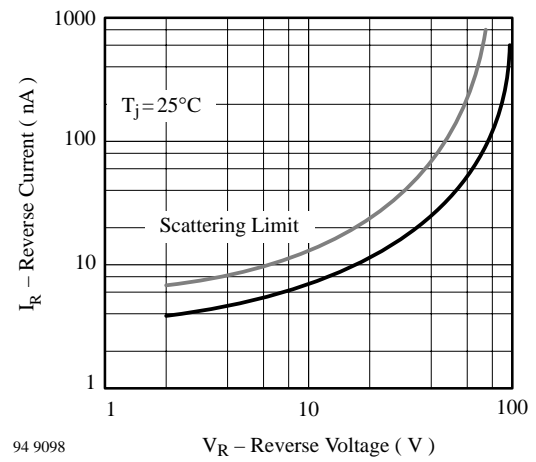


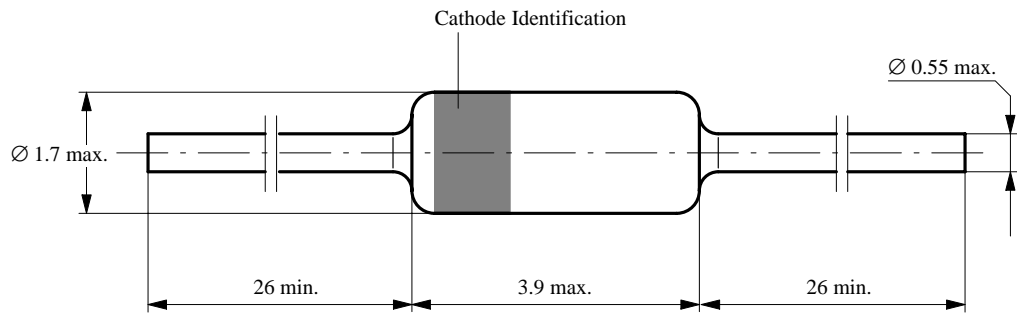
Figure 4. Reverse Current vs. Reverse Voltage

Dimensions in mm

technical drawings according to DIN specifications

94 9366

Standard Glass Case
54 A 2 DIN 41880
JEDEC DO 35
Weight max. 0.3g





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems
with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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